solution, and not on substrate surfaces. It is desired to produce a graphene layer either at the wafer level, i.e. over the entire area of a wafer, or in a targeted manner at an already existing topology of a wafer. The production of a graphene layer at wafer level, however, appears to be the most promising.

It is the problem of the present invention, therefore, to overcome the drawbacks of the prior art and to provide an improved method and/or an improved device for the transfer of a transfer layer. In particular, it is the problem of the present invention to ensure that the transfer layer is not destroyed or damaged, in particular not due to high-energy ions.

~~The present invention is solved with the features of the coordinated claims. Advantageous developments of the invention are specified in the sub-claims.~~

According to a first aspect of the present invention, there is provided a method for the transfer of a transfer layer, in particular a graphene layer, from one substrate, in particular from a growth substrate, to a carrier substrate, wherein the transfer takes place by means of an electromagnetic force, wherein the transfer layer and/or the substrate is charged with negative charge carriers, the carrier substrate is charged with ions, wherein the ions are charged oppositely to the negative charge carriers, between the transfer layer and/or the substrate and the carrier substrate due to the oppositely charged ions and the negative charge carriers a force is generated.

According to a second aspect of the present invention, there is provided a device for the transfer of a transfer layer from a substrate, in particular from a growth substrate, with the above a method, to a carrier substrate, wherein the transfer layer can be transferred by means of an electromagnetic force.

All combinations of at least two features specified in the description, in the claims and/or the drawings also fall within the scope of the invention. In the stated value ranges, values lying within the stated limits should also be deemed to be disclosed as limiting values and can be claimed in any combination.

The subject-matter as per embodiments of the invention is a method for the transfer of a transfer layer, in particular a graphene layer, from one substrate, in particular from a growth substrate, to a carrier substrate, wherein the transfer takes place by means of an electromagnetic force.

The subject-matter as per embodiments of the invention is also a device for the transfer of a transfer layer, in particular a graphene layer, from one substrate, in particular from a growth substrate, to a carrier substrate, wherein the transfer layer can be transferred by means of an electromagnetic force.

The electromagnetic force is preferably an electrostatic force, which acts between ions in the carrier substrate and the transfer layer, in particular the graphene layer correspondingly charged with opposite polarity. The ions are preferably positively charged in the carrier layer and the transfer layer is charged negatively.